

MOSFET - Power, Single N-Channel, D²PAK7 150 V, 7 mΩ, 121 A

NTBGS6D5N15MC

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- Lowers Switching Noise/EMI
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

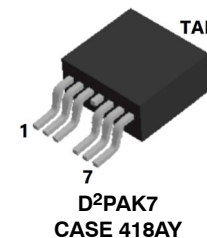
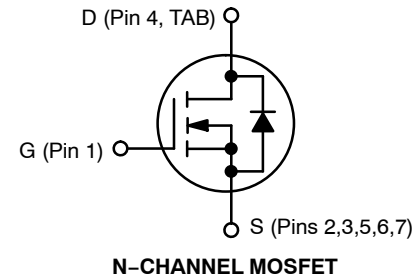
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	150	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^{\circ}\text{C}$	I_D	121	A
Power Dissipation $R_{\theta JC}$ (Note 2)			P_D	238	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	15	A
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)			P_D	3.7	W
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}, t_p = 10 \mu\text{s}$		I_{DM}	1800	A
Operating Junction and Storage Temperature			T_J, T_{stg}	-55 to +175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	198	A
Single Pulse Drain-to-Source Avalanche Energy ($I_L = 60 A_{pk}, L = 0.1 \text{ mH}$)			E_{AS}	180	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using a 1 in², 1 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
150 V	7 mΩ @ 10 V	121 A
	8.7 mΩ @ 8 V	



MARKING DIAGRAM

AYWWZZ
NTBG
S6D5N15

NTBGS6D5N15 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Number

ORDERING INFORMATION

Device	Package	Shipping [†]
NTBGS6D5N15MC	D ² PAK7 (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	0.6	°C/W
Junction-to-Ambient – Steady State (Note 1, 2)	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\text{ }\mu\text{A}$, ref to 25°C		59.62		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 120\text{ V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 379\text{ }\mu\text{A}$	2.5	3.5	4.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 250\text{ }\mu\text{A}$, ref to 25°C		-9.53		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 69\text{ A}$		5.5	7	m Ω
		$V_{GS} = 8\text{ V}, I_D = 34\text{ A}$		5.9	8.7	
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 60.5\text{ A}$		88		S
Gate-Resistance	R_G	$T_A = 25^\circ\text{C}$		1.1		Ω

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 75\text{ V}, f = 1\text{ MHz}$		4745		pF
Output Capacitance	C_{OSS}			1370		
Reverse Transfer Capacitance	C_{RSS}			10.3		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}, I_D = 69\text{ A}$		57		nC
Threshold Gate Charge	$Q_{G(TH)}$			16		
Gate-to-Source Charge	Q_{GS}			27		
Gate-to-Drain Charge	Q_{GD}			7		
Output Charge	Q_{OSS}			171		
		$V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}$				nC

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}, I_D = 69\text{ A}, R_G = 6\text{ }\Omega$		34		ns
Rise Time	t_r			75		
Turn-Off Delay Time	$t_{d(OFF)}$			39		
Fall Time	t_f			6		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 69\text{ A}$	$T_J = 25^{\circ}\text{C}$		0.92	1.2	V
			$T_J = 125^{\circ}\text{C}$		0.82		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 69\text{ A}$			74		ns
Charge Time	t_a				53		
Discharge Time	t_b				22		
Reverse Recovery Charge	Q_{RR}					141	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

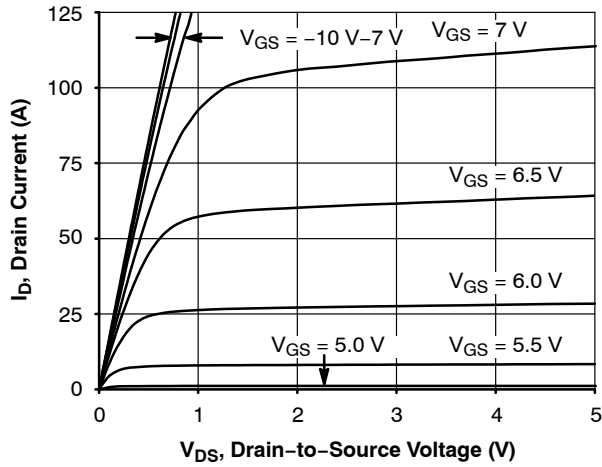


Figure 1. On-Region Characteristics

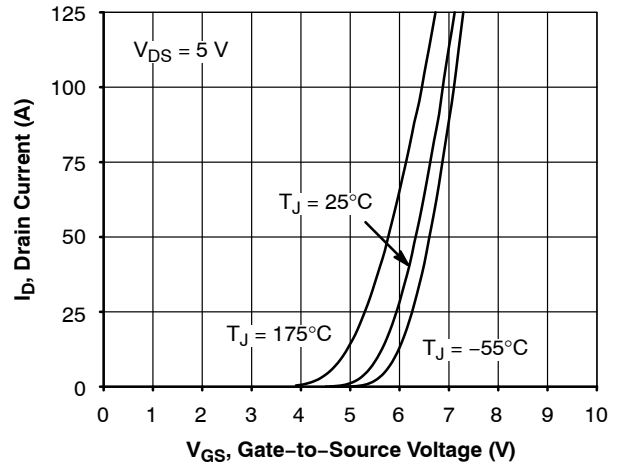


Figure 2. Transfer Characteristics

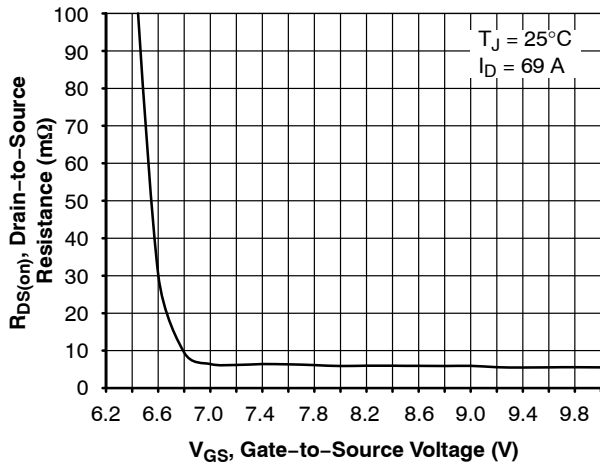


Figure 3. On-Resistance vs. Gate-to-Source Voltage

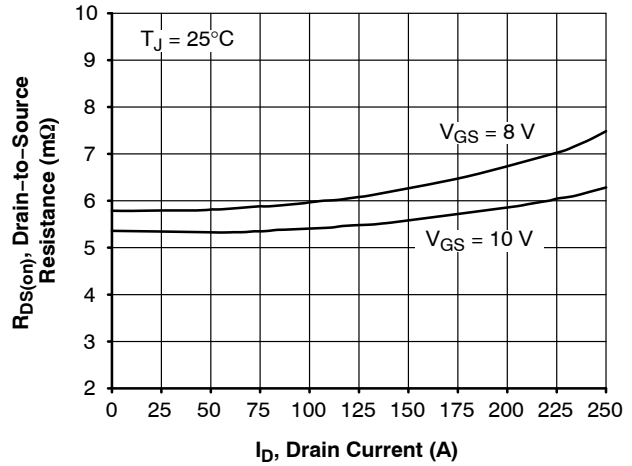


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

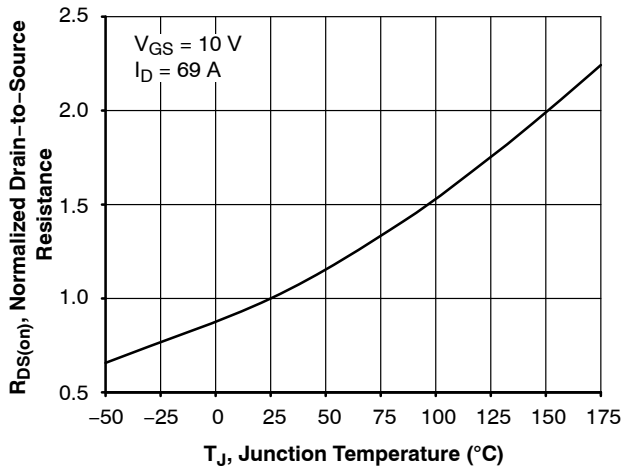


Figure 5. On-Resistance Variation vs. Temperature

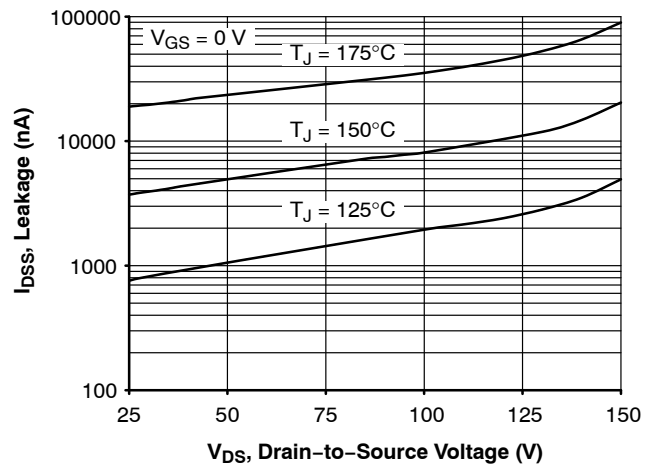


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS (Continued)

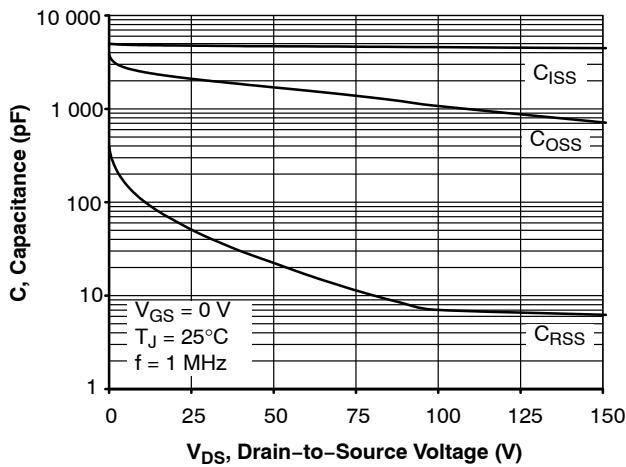


Figure 7. Capacitance Variation

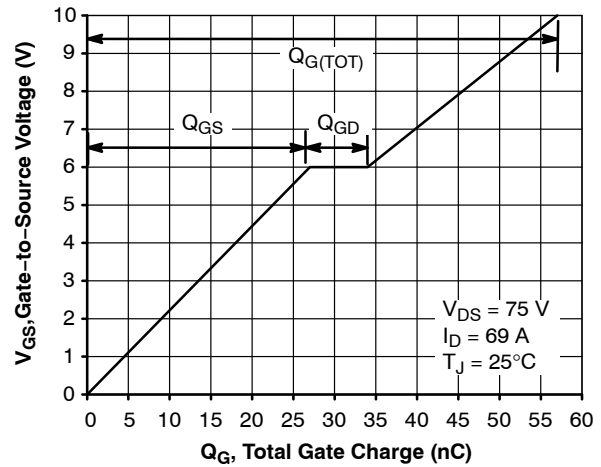


Figure 8. Gate-to-Source vs. Total Charge

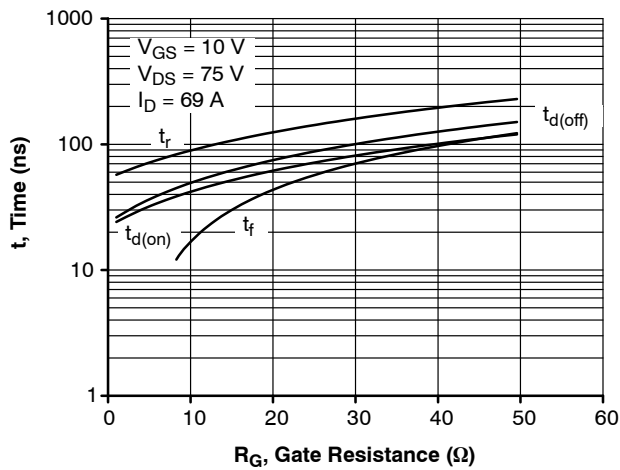


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

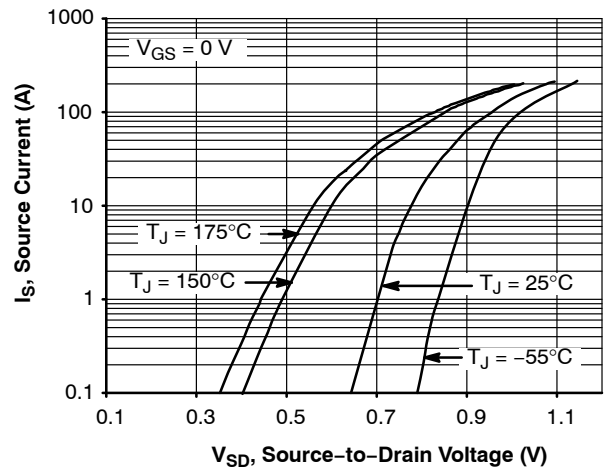


Figure 10. Diode Forward Voltage vs. Current

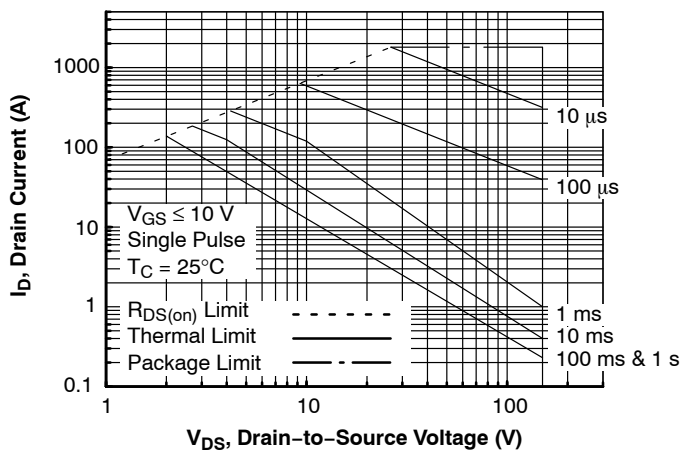


Figure 11. Maximum Rated Forward Biased Safe Operating Area

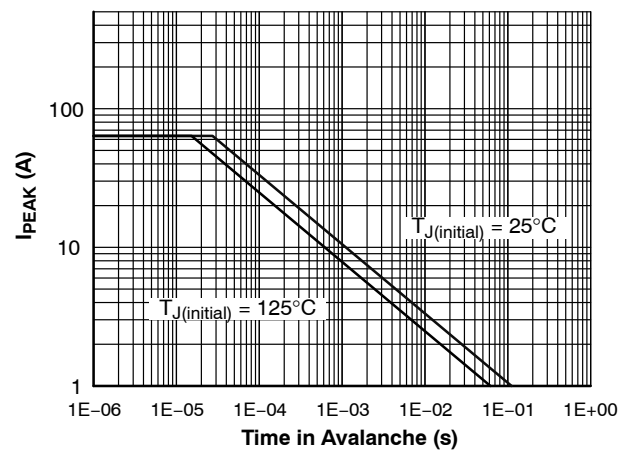


Figure 12. Maximum Drain Current vs. Time in Avalanche

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TYPICAL CHARACTERISTICS (Continued)

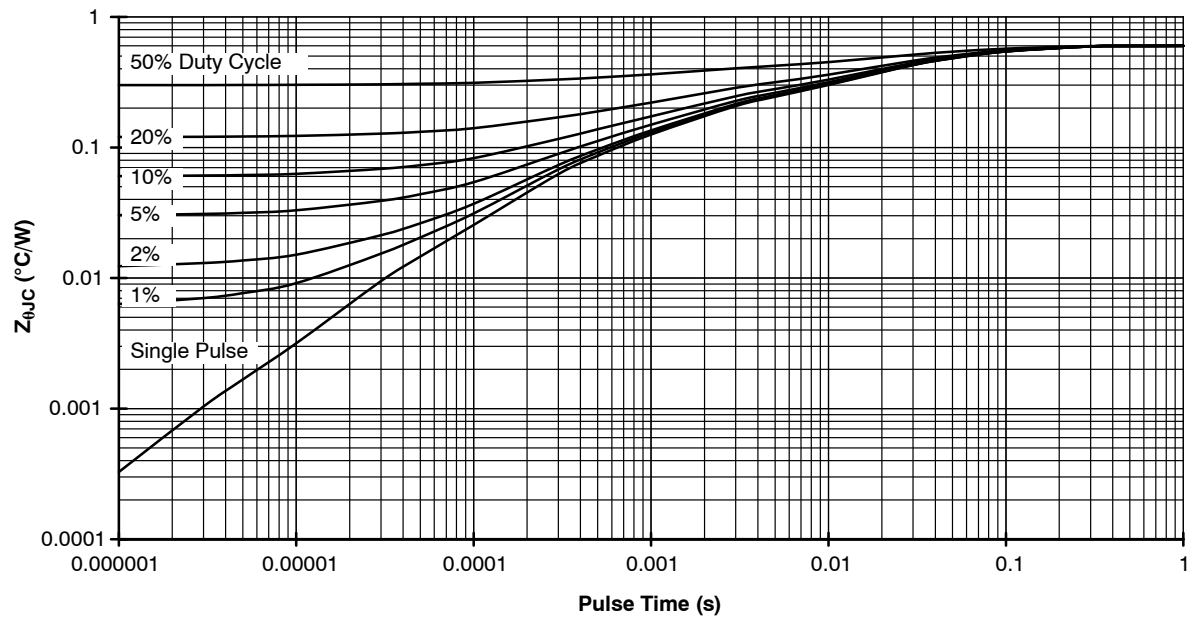


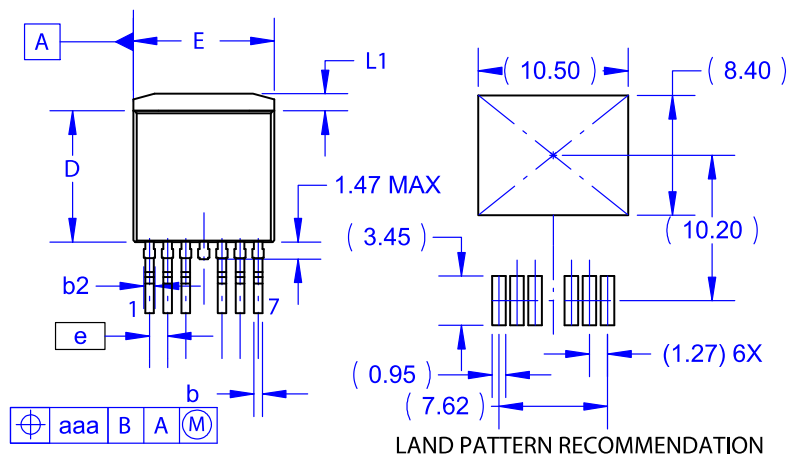
Figure 13. Thermal Response

D2PAK7 (TO-263 7 LD)

CASE 418AY

ISSUE C

DATE 15 JUL 2019

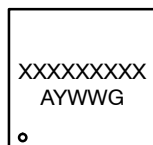


NOTES:

- A. PACKAGE CONFORMS TO JEDEC TO-263 VARIATION CB EXCEPT WHERE NOTED.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. OUT OF JEDEC STANDARD VALUE.
- D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- F. LAND PATTERN RECOMMENDATION PER IPC. TO127P1524X465-8N.

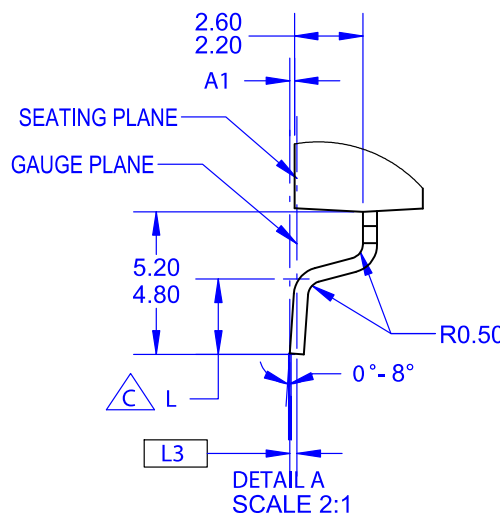
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	0.00	0.10	0.20
b2	0.70	0.80	0.90
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.20	1.30	1.40
D	9.00	9.20	9.40
D1	7.70	~	~
E	9.70	9.90	10.20
E1	8.38	8.58	8.78
e	~	1.27	~
H	15.10	15.40	15.70
L	2.44	2.64	2.84
L1	1.00	1.20	1.40
L3	~	0.25	~
aaa	~	~	0.25

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



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